



Subject card

Subject name and code	Solid state electronics and nanoelectronics, PG_00037001						
Field of study	Nanotechnology						
Date of commencement of studies	October 2023	Academic year of realisation of subject			2023/2024		
Education level	second-cycle studies	Subject group			Optional subject group Subject group related to scientific research in the field of study		
Mode of study	Full-time studies	Mode of delivery			at the university		
Year of study	1	Language of instruction			English		
Semester of study	2	ECTS credits			2.0		
Learning profile	general academic profile	Assessment form			exam		
Conducting unit	Department of Solid State Physics -> Faculty of Applied Physics and Mathematics						
Name and surname of lecturer (lecturers)	Subject supervisor	dr inż. Kamil Kolincio					
	Teachers	dr inż. Kamil Kolincio					
Lesson types and methods of instruction	Lesson type	Lecture	Tutorial	Laboratory	Project	Seminar	SUM
	Number of study hours	30.0	0.0	0.0	0.0	0.0	30
	E-learning hours included: 0.0						
Learning activity and number of study hours	Learning activity	Participation in didactic classes included in study plan		Participation in consultation hours		Self-study	SUM
	Number of study hours	30		2.0		18.0	50
Subject objectives	The aim of the course is to acquire knowledge, skills and competence in the field of solid state electronics and nanoelectronics.						
Learning outcomes	Course outcome	Subject outcome			Method of verification		
	K7_W03	Possessing the knowledge of the newest trends and discoveries in the field of nanostructures			[SW1] Assessment of factual knowledge		
	K7_K09	Understanding non-technical aspects and effects of engineering activities.			[SK2] Assessment of progress of work		
	K7_U07	Ability to use the obtained knowledge in other fields of science			[SU1] Assessment of task fulfilment		
	K7_W02	Possessing the detailed knowledge of the selected field of nanotechnology and related scientific disciplines			[SW1] Assessment of factual knowledge		

Subject contents	<p>1. Introduction.</p> <p>2. Physics and properties of solids - a review</p> <p>2.1. Density of states in 0D, 1D, 2D and 3D materials.</p> <p>2.2. Band structure of solids: free electron, nearly free electron and tight binding model.</p> <p>2.3. Energy bands and carrier concentration in thermal equilibrium.</p> <p>2.4. Electrical and thermal conduction in solids: carrier transport phenomena.</p> <p>2.5. Kinetic phenomena in semiconductors.</p> <p>3. Metal-semiconductor junctions and p-n junctions.</p> <p>4. Diodes: Schottky diode, p-n diode, MIS, MOS, tunnel diode, resonant-tunneling diode.</p> <p>5. Transistors: bipolar, FET, hot-electron HET and THET, single-electron transistor.</p> <p>6. Light emitting diodes and lasers.</p> <p>6.1. Light emitting diodes.</p> <p>6.2. Semiconductor lasers.</p> <p>6.3. Quantum-cascade laser.</p> <p>7. Photodetectors and solar cells.</p> <p>8. Tunnel phenomena in superconductors: Josephson junction.</p> <p>9. Spintronic devices.</p> <p>10. Semiconductor technology.</p> <p>10.1. Crystal growth and epitaxy.</p> <p>10.2. Film formation.</p> <p>10.3. Lithography and etching.</p> <p>10.4. Impurity doping.</p>		
Prerequisites and co-requisites	Completed courses in the field of basics of nanotechnology and solid state physics (or physics of materials).		
Assessment methods and criteria	Subject passing criteria	Passing threshold	Percentage of the final grade
	written test	50.0%	100.0%

Recommended reading	Basic literature	1. S.O. Kasap "Principles of electronic materials and devices", McGraw-Hill, 2006, 3rd ed. (EI 178223-00-00/01) 2. S.M. Sze, Kwok K. Ng, Physics of Semiconductor Devices, John Wiley & Sons, 2007, 3rd ed. (FM 304796-00-00/01)
	Supplementary literature	1. S.M. Sze, M.K. Lee Semiconductor Devices, Physics and Technology, John Wiley & Sons, 2012, 3rd ed.
	eResources addresses	Adresy na platformie eNauczenie: Solid State Electronics and Nanoelectronics summer 2024 - Moodle ID: 37294 https://enauczenie.pg.edu.pl/moodle/course/view.php?id=37294
Example issues/ example questions/ tasks being completed	Describe metal-semiconductor junction Describe MOS diode Describe single electron transistor Describe quantum-cascade laser	
Work placement	Not applicable	